

ABSTRACT

Methods for making a nonvolatile memory device, such as an NROM device that has an oxide-nitride-oxide layer beneath at least one word line structure, are disclosed. The oxide-nitride-oxide layer is in the form of a plurality of oxide-nitride block structures disposed over an oxide layer, with each of the oxide-nitride block structures overlapping two adjoining bit lines. A dielectric resolution enhancement coating technique is performed to precisely control the oxide-nitride block structure dimensions.